

## AMENDMENTS TO THE CLAIMS

1. (Currently Amended) An apparatus using vapor phase deposition comprising:  
a deposition part, which comprises:
  - a process chamber;
  - a substrate holder installed in the process chamber for supporting a loaded substrate;
  - a substrate temperature controller installed in the substrate holder for controlling the temperature of the substrate; and
  - a shower head installed opposite the substrate holder in the process chamber to uniformly distribute organic source vapors to be used for a deposition reaction onto the substrate; anda source part, which comprises:
  - a source chamber for generating organic source vapors to be supplied to the shower head;
  - a transfer gas supply source for supplying transfer gas that is used to transfer organic source vapors to the process chamber;
  - a source heater which surrounds the source chamber and allows organic materials to evaporate to be organic source vapors in the source chamber; ~~and~~
  - a transfer gas distributor installed in the source chamber, wherein the transfer gas distributor is a conic block or a conic plate with an apex aligned with a transfer gas inlet and pointing towards the transfer gas inlet; and
  - a diluted gas supply source, from which diluted gas is supplied to combine with the transfer gas before entering the process chamber and after the transfer gas leaving the source chamber in order to control pressure of the process chamber.
2. (Currently Amended) The apparatus of claim 1, further comprising a shower curtain, which is installed between the shower head and the substrate holder to surround the substrate holder.
3. (Previously Presented) The apparatus of claim 1, further comprising:

a transfer gas transfer line which is extended from the transfer gas supply source into the source chamber and includes the transfer gas inlet, which is formed in a portion extended into the source chamber of the transfer gas transfer line and allows the transfer gas to enter the source chamber; and

an organic source vapor transfer line which is extended from the shower head into the source chamber and includes an organic source vapor outlet, which allows the organic source vapors transferred by the transfer gas to exit the source chamber.

4. (Previously Presented) The apparatus of claim 3, wherein the transfer gas distributor distributes source gas fed from the transfer gas inlet.

5. (Cancelled)

6. (Original) The apparatus of claim 3, wherein the source heater is expanded to surround the organic source vapor transfer line.

7. (Cancelled)

8. (Original) The apparatus of claim 1, further comprising a regulator for controlling the flow rate and speed of fluids fed into the process chamber.

9. (Original) The apparatus of claim 1, comprising a plurality of source chambers for generating different types of organic source vapors and further comprising:

a plurality of transfer lines, which are installed to allow different organic vapors to sequentially enter the process chamber or bypass using time-division; and

a plurality of valves, which are installed to use the transfer lines by time-division.

10. (Previously Presented) The apparatus of claim 9, wherein the source heater is expanded to heat the transfer lines and the valves.

11. (Currently Amended) A method using organic vapor phase deposition comprising:

generating first organic source vapors by heating a source chamber containing a first organic source material;

transferring the first organic source vapors by a transfer gas supplied via a transfer line, which is maintained at a constant temperature to prevent condensation of the first organic source vapors, to a shower head of a process chamber, wherein the transfer gas is distributed to the source chamber by a transfer gas distributor installed in the source chamber, the transfer gas distributor being a conic block or a conic plate with an apex aligned with a transfer gas inlet and pointing towards the transfer gas inlet;

combining diluted gas with the transfer gas before entering the process chamber and after the transfer gas leaving the source chamber in order to control pressure of the process chamber;

causing a deposition reaction by distributing the first organic source vapors transferred via the shower head onto a substrate that is loaded at a position opposite the shower head; and purging the process chamber after the vapor deposition is completed.

12. (Original) The method of claim 11, further comprising sequentially repeating causing a deposition reaction and purging the process chamber.

13. (Currently Amended) The method of claim 11, to form multi-component organic thin films, further comprising:

forming second organic source vapors by heating an additional source chamber containing ~~the first organic material and~~ a second organic material;

transferring the second organic source vapors via another transfer line, which is maintained at a constant temperature to prevent condensation of the second organic source vapors, to the shower head of the process chamber;

causing a second deposition reaction by distributing the second organic source vapors transferred via the shower head onto the substrate that is loaded at a position opposite the shower head; and

second-purging the process chamber after the second vapor deposition is conducted on the substrate.

14. (Original) The method of claim 13, wherein the first organic source vapors and the second organic source vapors are alternately supplied to the process chamber using time-division by about 0.01 second to several hours.